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(54) **TRANSISTOR DV/DT CONTROL CIRCUIT**

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(57) **ABSTRACT**

Circuits and methods that control a rate of change of a drain voltage as a function of time in a transistor are disclosed. In one aspect, the circuit includes a transistor having a gate terminal that controls operation of the transistor, and a control circuit coupled to the gate terminal and arranged to change a voltage at the gate terminal at a first rate of voltage with respect to time from a first voltage to a first intermediate voltage, and further arranged to change the voltage at the gate terminal at a second rate of voltage with respect to time from the first intermediate voltage to a second intermediate voltage, where the first rate is different than the second rate.

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